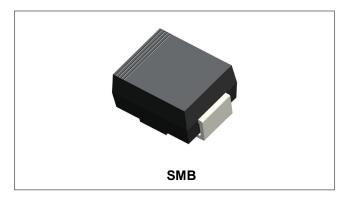






10BQ060 SCHOTTKY RECTIFIER



Features

- Small foot print, surface moutable
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Disk Drives
- Switching power supply
- Redundant power subsystems
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Battery Charging

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$egin{array}{c} V_{RRM} \ V_{RWM} \ \end{array}$	-	60	V
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @T _C =103°C, rectangular wave form	1.0	Α
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine pulse, T _C =25°C	50	Α

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V_{F1}	@ 1 A, Pulse, T _J = 25 °C	0.55	0.60	V
		@ 2 A, Pulse, T _J = 25 °C	0.67	0.76	V
	V_{F2}	@ 1 A, Pulse, T _J = 125 °C	0.48	0.57	V
		@ 2 A, Pulse, T _J = 125 °C	0.60	0.69	V
Reverse Current*	I _{R1}	@V _R = Rated V _R , Pulse, T _J = 25 °C	0.01	1	mA
	I _{R2}	@V _R = Rated V _R , Pulse, T _J = 125 °C	5	10	mA
Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	45	62	pF
Series Inductance	Ls	Measured lead to lead 5 mm from package body	2.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

^{*} Pulse width < 300 μs, duty cycle < 2%

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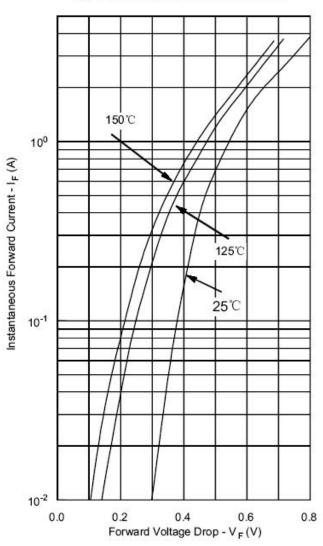


Thermal-Mechanical Specifications:

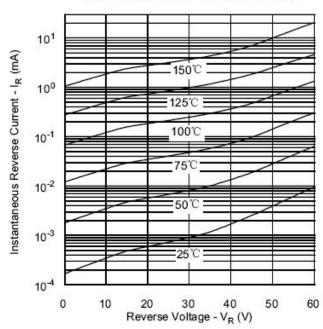
Characteristics	Symbol	Condition	Specification Uni	
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Lead	R ₀ JL	-	36	°C/W
Approximate Weight	wt	-	0.09	g
Case Style	SMB			

Ratings and Characteristics Curves

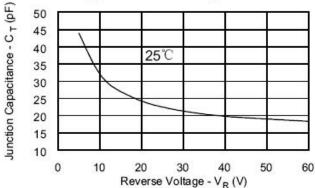
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance



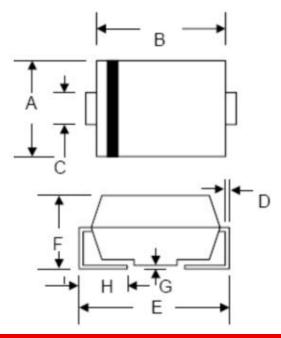
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Mechanical Dimensions SMB



OVMDOL	Millimeters		Inches		
SYMBOL	Min.	Max.	Min.	Max.	
Α	3.30	3.94	0.130	0.155	
В	4.06	4.70	0.160	0.185	
С	1.80	2.20	0.071	0.087	
D	0.152	0.305	0.006	0.012	
E	4.80	5.59	0.189	0.220	
F	2.10	2.60	0.083	0.102	
G	0.051	0.203	0.002	0.008	
Н	0.76	1.52	0.030	0.060	

Ordering Information

Device	Package	Shipping	
10BQ060	SMB (Pb-Free)	3000pcs / reel	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram



Where XXXXX is YYWWL

 SB1H
 = Part Name

 YY
 = Year

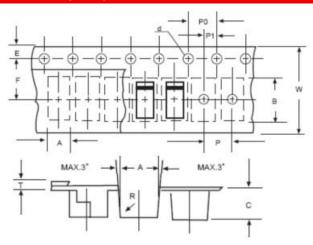
 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

Carrier Tape Specification SMB



SYMBOL	Millimeters		
	Min.	Max.	
Α	2.97	3.17	
В	5.70	5.90	
С	2.32	2.52	
d	1.40	1.60	
Е	1.40	1.60	
F	5.60	5.70	
Р	3.90	4.10	
P0	3.90	4.10	
P1	1.90	2.10	
T	0.25	0.35	
W	11.80	12.20	

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